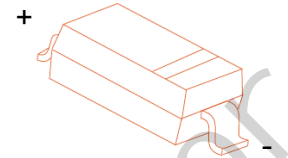


FEATURES

- Low forward voltage drop
- Guard ring construction for transient protection
- Negligible reverse recovery time
- Low reverse capacitance

SOD-123



MARKING: NRVB130T1G S3*

Maximum Ratings and Electrical Characteristics, Single Diode @T_A=25°C

Parameter	Symbol	MBR130T	Unit
Peak Repetitive Peak reverse voltage	V _{RRM}	30	V
Working Peak	V _{RWM}		
DC Blocking Voltage	V _R		
RMS Reverse Voltage	V _{R(RMS)}	28	V
Forward Continuous Current	I _{FM}	1	A
Repetitive Peak Forward Current @t≤1.0s	I _{FRM}	1.5	A
Power Dissipation	P _d	500	mW
Thermal Resistance Junction to Ambient	R _{θJA}	250	°C/W
Storage temperature	T _{STG}	-65~+150	°C

Electrical Ratings @T_A=25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	V _{(BR)R}	30			V	I _R =100μA
Forward voltage	V _F			0.37 0.60	V	I _F =20mA I _F =200mA
Reverse current	I _{RM}			5.0	μA	V _R =30V
Capacitance between terminals	C _T		50		pF	V _R =0V, f=1.0MHz
Reverse Recovery Time	t _{rr}		10		ns	I _F =I _R =200mA I _{rr} =0.1X I _R , R _L =100Ω

Typical Characteristics

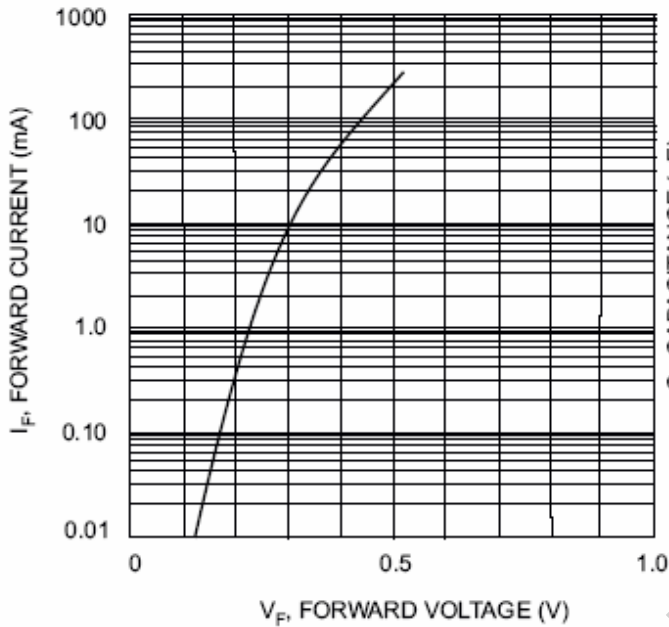


Fig. 1 Typical Forward Characteristics

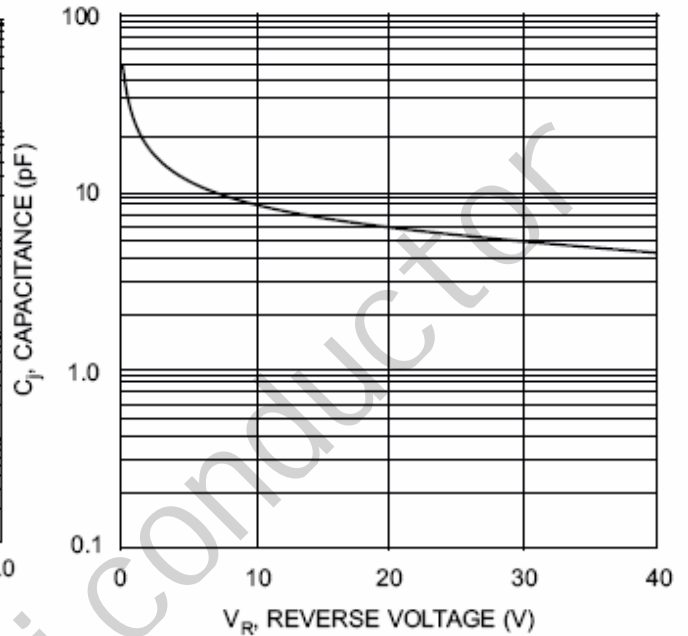


Fig. 2 Typ. Junction Capacitance vs Reverse Voltage